

Title (en)

ORGANIC THIN FILM TRANSISTOR AND METHOD FOR PRODUCING SAME

Title (de)

ORGANISCHER DÜNNSCICHT-TRANSISTOR UND VERFAHREN ZUR HERSTELLUNG DESSELBEN

Title (fr)

TRANSISTOR À COUCHE MINCE ORGANIQUE ET PROCÉDÉ DE FABRICATION DE CELUI-CI

Publication

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Application

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Abstract (en)

[origin: CA3127002A1] The invention relates to an organic thin film transistor (OTFT), particularly a thin film field effect transistor (OFET), having a source electrode, a drain electrode, a gate electrode arranged in top gate arrangement, and an organic semiconductor functional layer, wherein the source electrode, the drain electrode and the gate electrode are arranged in a co-planar layer structure, wherein the organic thin film transistor has an intermediate layer for capacitive decoupling of the gate electrode from the source electrode and/or from the source electrode.

IPC 8 full level

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